



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- ESD Protected Up To 2KV
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: DFN3030-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish NiPdAu over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.0172 grams (approximate)

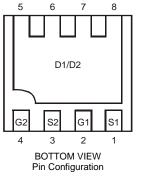
NEW PRODUCT

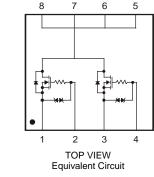




ESD PROTECTED TO 2kV

Bottom View





Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Top View

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	20	V
Gate-Source Voltage		Vgss	±12	V	
Continuous Drain Current (Note 1)	Steady State	TA = 25°C TA = 70°C	lD	6.1 5.2	A
Pulsed Drain Current		IDМ	27	А	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	Po	0.92	W
Thermal Resistance, Junction to Ambient @TA = 25°C	Reja	136	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	D°

Notes: 1. Device mounted on FR-4 PCB with minimum recommended pad layout.

2. No purposefully added lead.

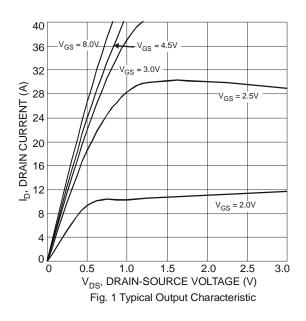
3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

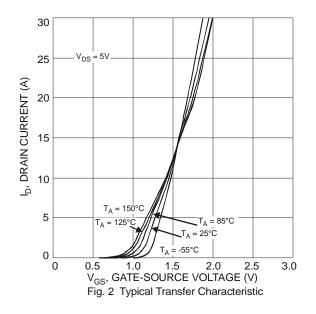


Electrical Characteristics @T_A = 25°C unless otherwise specified

			-			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	-	-	±10	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$
Gate-Source Breakdown Voltage	BV _{SGS}	±12	-	-	V	$V_{DS} = 0V$, $I_G = \pm 250 \mu A$
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	0.35	-	0.95	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
		-	17	23	27 m Ω	$V_{GS} = 4.5V, I_D = 6.5A$
Static Drain-Source On-Resistance	R _{DS (ON)}	-	20 25	27 34		$V_{GS} = 2.5V, I_D = 5.5A$
		-				$V_{GS} = 1.8V, I_D = 3.5A$
Forward Transfer Admittance	Y _{fs}	-	10	-	S	$V_{DS} = 10V, I_D = 5A$
Diode Forward Voltage	V _{SD}	-	0.7	1.0	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	-	143	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	Coss	-	74	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	29	-	pF	
Gate Resistance	R _g	-	202	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Qg	-	8.8	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Source Charge	Q _{gs}	-	1.4	-	nC	
Gate-Drain Charge	Q _{gd}	-	3.0	-	nC	$I_D = 6.5A$
Turn-On Delay Time	t _{D(on)}	-	53	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_L = 10\Omega, R_G = 6\Omega$
Turn-On Rise Time	tr	-	78	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	562	-	ns	
Turn-Off Fall Time	t _f	-	234	-	ns	

Notes: 4. Short duration pulse test used to minimize self-heating effect.







Γ_A = 150°C

T_A = 125°C T_A = 85°C

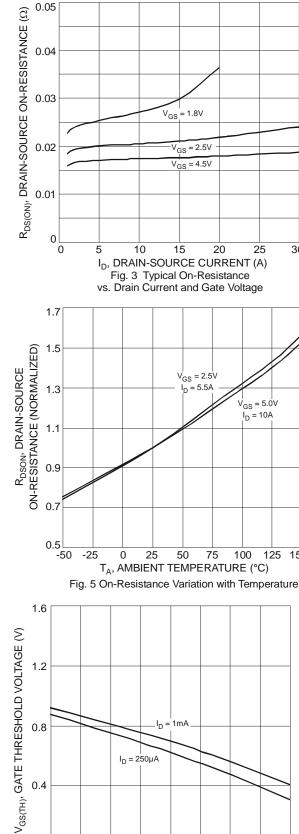
 $T_A = 25^{\circ}C$

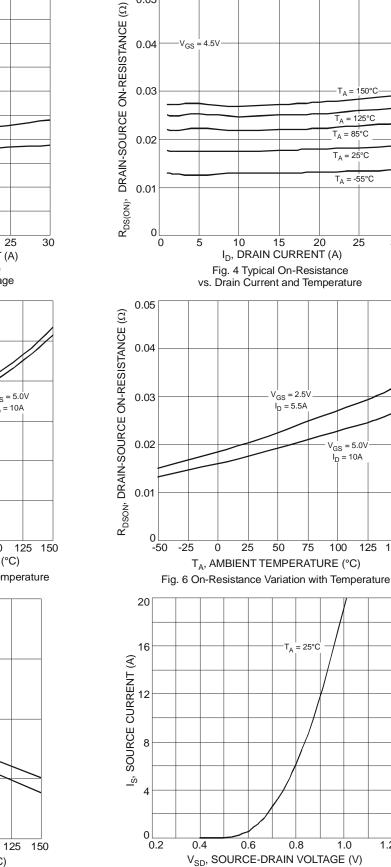
T_A = -55°C

25

30

125 150





0.05

0.04

4.5V V_{GS}

Fig. 7 Gate Threshold Variation vs. Ambient Temperature

100

0 -50 -25 0 25 50 75 T_A, AMBIENT TEMPERATURE (°C) DMG8601UFG Document number: DS31788 Rev. 4 - 2

1.2

1.0

Fig. 8 Diode Forward Voltage vs. Current



NEW PRODUCT

DMG8601UFG

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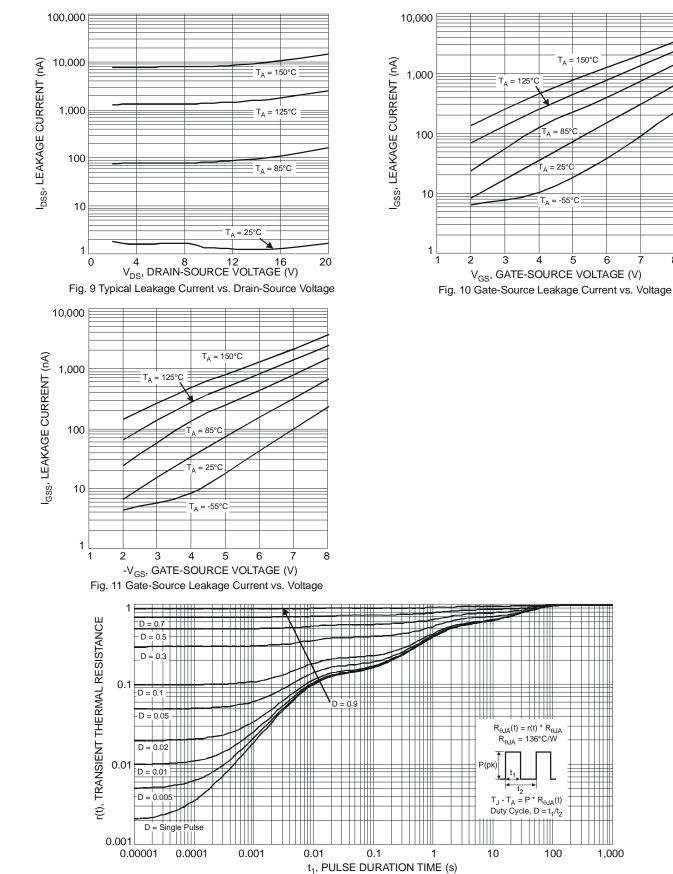


Fig. 12 Transient Thermal Response

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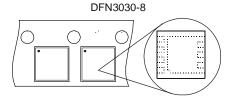
Ordering Information (Note 5)				
Part Number	Case	Packaging		
DMG8601UFG-7	DFN3030-8	3000/Tape & Reel		

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

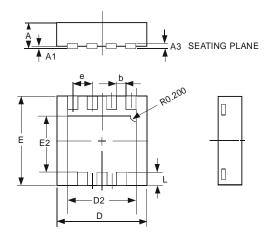
Marking Information



2N4 = Product marking code YYWW = Date code marking YY = Last digit of year (ex: 09 for 2009) WW = Week code 01 to 52

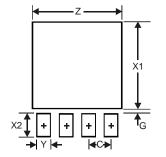


Package Outline Dimensions



DFN3030-8				
Dim	Min	Max	Тур	
Α	0.57	0.63	0.60	
A1	0	0.05	0.02	
A3	_	_	0.15	
b	0.29	0.39	0.34	
D	2.90	3.10	3.00	
D2	2.19	2.39	2.29	
е	_	_	0.65	
E	2.90	3.10	3.00	
E2	1.64	1.84	1.74	
L	0.30	0.60	0.45	
All D	All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.59
G	0.11
X1	2.49
X2	0.65
Y	0.39
С	0.65



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